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Guido, L.J., 59—January
Gutai, L., 1221—November

Haddad, N., 603—July
Haddock, T.B., 1257—November
Hajjar, J.-J.J., 1403—December
Hall, D.C., 59—January
Hall, E.L., 509—June
Hall., J.T., 815—August
Halliwell, M.A.G., 515—June
Hammarlund, B., 981—September
Hammerl, E., 1119—October
Hanafusa, H., 1021—October
Hang, T., 295—April
Hansson, G.V., 1033—October
Hardtdegen, H., 305—April
Harrington, W., 1043—October
Hasan, M.-A., 1033—October
Hatch, C.B., 515—June
Hauser, J.R., 671—July
Hayakawa, Y., 145—February
Haywood, S.K., 783—August
Hergeth, J., 471—May
Herman, M.H., 265—March
Herres, N., 555—June
Hiesinger, P., 555—June
Hirtz, J.P., 567—June
Ho, P., 509—June
Hodge, L.A., 345—April
Holonyak, N. Jr., 59—January
Hong, C.-H., 1141—October
Hong, R.-D., 829—August
Hong, S., 903—September
Hostalek, M., 305—April
Hsieh, K.C., 59—January
Hsieh, K.C., 249—March
Hsieh, K.Y., 1417—December
Hsu, C.C.-H., 721—July
Hsu, J.-K., 967—September
Hsu, T., 375—April
Hsu, T., 1027—October
Hsu, T., 1043—October
Hsu, T., 1089—October
Hu, M., 1265—November
Hu, S.J., 1319—November
Huang, C.J., 753—July
Huang, R.-T., 1313—November
Hughes, H.L., 449—May
Hughes, H.L., 665—July
Hummell, S.G., 1367—December
Hwang, Y.L., 1417—December
Hyland, S.L., 873—September

Ikeda, Y., 45—January
Inam, A., 117—January
Ioannou, D.E., 449—May
Iyer, S., 111—January

Jantz, W., 747—July
Jaros, M., 35—January
Jellison, G.E. Jr., 105—January
Jen, C.K.C., 629—July
Jennings, S.R., 617—July
Jensen, K.F., 453—May
Jesser, W.A., 1289—November
Jia, Q.X., 443—May
Jia, Y., 1083—October
Jiran, E., 1155—November
Johnson, G.D., 463—May
Johnson, R.I., 241—March
Jones, E.D., 533—June
Jones, E.D., 989—September
Jones, G.W., 89—January
Jones, K.A., 1247—November
Juang, C.-L., 1313—November

Kadota, Y., 219—March
Kalainathan, S., 1135—October
Kalem, S., 249—March
Kalkur, T.S. 29—January
Kalnitsky, A., 131—February
Kalokitis, D., 117—January
Kaloyeras, A.E., 271—March
Kanber, H., 1265—November
Kaoukab, J., 187—February
Kataoka, K., 429—May
Kato, S., 739—July
Katoda, T., 407—May
Kaufel, G., 747—July
Kawanaka, M., 575—June
Kawanaka, M., 795—August
Kawata, M., 407—May
Kear, B.H., 357—April
Kearley, M.Q., 323—April
Kegel, G.H.R., 629—July
Keller, R.R., 865—September
Kellert, F.G., 311—April
Kellert, F.G., 1425—December
Kerns, S.E., 671—July
Kesan, V.P., 265—March
Ketterson, A.A., 249—March
Kibbler, A., 95—January
Kibbler, A., 825—August
Kibuule, P.M., 689—July
Kikkawa, T., 795—August
Kikuta, K., 795—August
Kim, B., 1177—November

Kim, B., 1185—November
Kim, C.-T., 1141—October
Kim, C.S., 889—September
Kim, H.K., 139—February
Kim, K.-B., 1221—November
Kim, S.S., 151—February
King, A.H., 1177—November
King, R.M., 865—September
Kiunke, W., 1119—October
Kjebon, O., 981—September
Klaasen, W.A., 1111—October
Klausmeier-Brown, M.E., 7—January
Kleverman, M., 837—August
Kloesel, K., 689—July
Klonaris, N.S., 1201—November
Knall, J., 1033—October
Knox, W.H., 937—September
Ko, D.H., 1171—November
Köhler, K., 747—July
Kohler, R.A., 689—July
Kolbas, R.M., 1417—December
Kolodzey, J., 249—March
Konagai, M., 1083—October
Kondow, M., 597—June
Kopf, R.F., 521—June
Koteles, E.S., 539—June
Krusius, J.P., 1145—October
Krzanowski, J.E., 919—September
Kuech, T.F., 277—March
Kumagawa, M., 145—February
Kumar, A., 481—May
Kuo, J.M., 521—June
Kuo, J.N., 393—April
Kurtz, S.R., 95—January
Kurtz, S.R., 825—August
Kurtz, S.R., 989—September
Kuznia, J.N., 561—June
Kwon, Y.-S., 1141—October

Lacquet, B.M., 809—August
Lacquet, B.M., 1383—December
Lai, W.C., 419—May
Lambropoulos, J.C., 895—September
Lareau, R.T., 1247—November
Larsen, C.A., 299—April
Laskar, J., 249—March
Lau, K.M., 967—September
Lawrence, R.K., 665—July
Lee Y.R., 543—June
Lee, H.S., 1247—November
Lee, J.H., 1417—December
Lee, Y.S., 591—June
Leitch, A.W.R., 1429—December
Lenahan, P.M., 425—May
Lengle, S.E., 413—May
Lewis, N., 509—June
Li, J.-J., 1339—December
Li, S.H., 299—April
Li, Y., 859—September
Liberman, V., 1239—November
Licata, T.J., 1239—November
Lin, J.-C., 581—June
Ling, S., 1161—November
Littlejohn, M.A., 1129—October
Livescu, G., 937—September
Lockwood, D.J., 657—July
Lokei, M., 305—April
Look, D.C., 773—August
Lopez, S., 1411—December
Lott, J.A., 989—September
Lourdudoss, S., 981—September
Lu, Y.C., 29—January
Lucovsky, G., 151—February
Lucovsky, G., 209—March
Luehrs, F., 271—March
Lundstrom, M.S., 7—January
Luo, H., 543—June
Lux-Steiner, M., 777—August
Lyo, S.K., 533—June
Lyons, M.H., 515—June

Maa, B.Y., 289—April
Maanaki, S., 111—January
Maeda, H., 801—August
Magee, C., 1043—October
Major, J.S. Jr., 59—January
Maldonado, J.R., 699—July
Manfra, M.J., 975—September
Marek, H., 363—April
Martin, P.A., 509—June
Martin, R.W., 783—August
Mason, N.J., 783—August
Matsuda, S., 739—July
Mattingly, M., 435—May
Maung, N., 323—April
Maung, N., 349—April
Mavalvala, N., 1323—November
McCaffrey, J.P., 657—July
McCarty, T., 111—January
McKnelly, L.T., 1213—November
McLarty, P.K., 449—May
Meaton, C., 323—April
Meehan, K., 59—January
Mei, Z., 1273—November
Melloch, M.R., 7—January
Melman, P., 539—June
Menu, E.P., 1367—December
Mercier, J., 253—March
Mercier, J., 1075—October
Michel, C., 363—April
Michel, J., 949—September
Mieno, F., 1095—October
Mii, T., 1281—November
Miklis, A., 305—April
Miller, J., 957—September
Miller, R.O., 413—May
Milnes, A.G., 139—February
Minagawa, S., 597—June
Miner, C.J., 1—January
Miyamoto, H., 201—February
Moellering, R.A., 181—February
Molassioti, A., 851—August
Moll, N.J., 385—April
Montgomery, V., 13—January
Moon, H.J., 1351—December
Moriwaki, M.M., 815—August
Morris, J.W. Jr., 1213—November
Morris, J.W. Jr., 1273—November
Moseley, A.J., 323—April
Moseley, A.J., 349—April
Moser, L., 1185—November
Müller, H.D., 555—June
Murdeshwar, N., 919—September
Muto, H., 739—July

Nadahara, S., 407—May
Nakahara, S., 413—May
Nakanishi, K., 739—July
Nakayama, H., 801—August
Nam, D.W., 59—January
Narayan, J., 481—May
Naseem H.A., 419—May
Nayak, D., 125—February
Nazar, L., 117—January
Neikirk, D.P., 265—March
Nelson, A.J., 481—May
Nelson, A.J., 1061—October
Nelson, J.S., 989—September
Nelson, R.W., 1257—November
Neudeck, G.W., 1111—October
Ngo, D., 689—July
Ning, T.H., 721—July
Nix, W.D., 903—September
Nix, W.D., 1231—November
Noh, D.W., 357—April
Norris, P.E., 295—April
Norris, P.E., 357—April
Norton, D.P., 367—April
Numasawa, Y., 45—January

O'Brien, T., 859—September
Ogata, H., 1021—October
Oh, J.E., 435—May
Ohata, K., 201—February
Ohmachi, Y., 219—March
Ohmi, T., 1065—October
Ohmine, T., 429—May
Okamoto, A., 201—February
Oladipupo, A., 689—July
Olajos, J., 837—August
Oliver, W.C., 881—September
Olson, J.M., 95—January
Olson, J.M., 825—August
Omling, P., 837—August
Ortiz, A., 1411—December
Osburn, C.M., 67—January
Osgood, R.M. Jr., 1239—November
Otsuka, N., 543—June
Öztürk, M.C., 1129—October

Pachuta, S.J., 453—May
Parris, P., 337—April
Pascal, F., 187—February
Paz De Araujo, C.A., 29—January
Pendrick, V., 117—January
Perera, A.H., 1145—October
Perret, P., 1123—October
Peticolas, L.J. Jr., 413—May
Peugnet, A., 567—June

Pharr, G.M., 881—September
Pickering, C. 51—January
Podlesnik, D.V., 1239—November
Pohl, L., 305—April
Pollak, F.H., 283—March
Pollak, F.H., 295—April
Pollak, F.H., 399—May
Potemski, R., 277—March
Potts, J.E., 453—May
Price, W.E., 609—July
Puissant, C., 1123—October

Qadri, S.B., 543—June
Qian, R., 1027—October
Qian, R., 1043—October
Qian, R., 1089—October

Raaijmakers, I.J., 1221—November
Rajan, K., 943—September
Rajan, K., 1009—October
Rajan, K., 1193—November
Ralston, J.D., 555—June
Ramasamy, P., 1135—October
Ramdas, A.K., 543—June
Rao, M.V., 789—August
Raubenheimer, D., 1429—December
Rauschenbach, K., 463—May
Ready, S.E., 241—March
Reed, S.T., 425—May
Reents, W. Jr., 1015—October
Regel, G.K., 305—April
Regolini, J.L., 253—March
Regolini, J.L., 1075—October
Regolini, J.L., 1123—October
Reif, R., 337—April
Reif, R., 1395—December
Reif, R., 1403—December
Reinhardt, F., 471—May
Reisman, A., 651—July
Reisman, A., 711—July
Reisman, A., 727—July
Reisman, A., 995—September
Ren, S.Y., 829—August
Renner, D., 1313—November
Reno, J.L., 549—June
Reynolds, C.L. Jr., 413—May
Ringel, S.A., 259—March
Robbins, D.J., 323—April
Robbins, D.J., 349—April
Robbins, V.M., 1425—December
Roedel, R.J., 1257—November
Rohatgi, A., 259—March
Rosencher, E., 101—January
Ross, C.A., 911—September
Rothemund, W., 555—June
Rothemund, W., 747—July
Rowan, L.G., 633—July
Russell, P., 1129—October

Sacks, R.N., 283—March
Sadamoto, M., 1395—December
Sadwick, L., 637—July
Saitou, Y., 145—February
Sakamoto, M., 45—January
Samarth, N., 543—June
Sanchez, J.E. Jr., 1213—November
Sandwick, T., 1193—November
Sangsingkeow, P., 105—January
Sasaki, S., 739—July
Sato, Y., 429—May
Saunders, M-L., 757—July
Saxena, A.N., 271—March
Schachter, R., 363—April
Schirber, J.E., 533—June
Schlesinger, T.E., 139—February
Schmälzlin, J., 555—June
Schmidt, M.T., 1239—November
Schneider, J., 555—June
Scholz, F., 851—August
Schubert, P.J., 1111—October
Schubert., E.F., 521—June
Schulz, K.J., 581—June
Schwartz, P.V., 1051—October
Schweizer, Th., 747—July
Scilla, G., 277—March
Seaward, K.L., 385—April
Serreze, H.B., 363—April
Setalvad, T., 1221—November
Sethi, R.B., 231—March
Sha, Y.G., 159—February
Sha, Y.G., 761—August
Sha, Y.G., 1303—November
Shand, B.A., 51—January
Shen, G.D., 1033—October
Shen, H., 283—March
Shen, H., 295—April
Shen, H., 399—May
Shen, J., 829—August
Shepherd, F.R., 1—January
Shibata, T., 1065—October
Shine, M.C., 1273—November
Shiozawa, J., 407—May
Siegrist, T., 235—March
Sinclair, R., 1171—November
Singh, R., 481—May
Singh, R., 1061—October
Sirco, D., 249—March
Smith, D.D., 757—July
Smith, D.L., 19—January
Smith, F.W., 1323—November
Smith, G.W., 51—January
Solomon, H.D., 929—September
Somekh, R.E., 911—September
Sone, J., 575—June
Sone, J., 795—August
Soto, G., 1411—December
Speckman, D.M., 495—May
Springthorpe, A.J., 1—January
Stahlbush, R.E., 665—July
Stassinopulos, E.G., 689—July
Steinberg, T., 1323—November
Stephenson, L.L., 549—June
Sterner, D., 1185—November
Stevie, F., 1015—October
Stickle, W.F., 385—April
Stillman, G.E., 331—April
Stoebe, T.G., 1351—December
Streetman, B.G., 265—March
Streetman, B.G., 1333—December
Stringfellow, G.B., 299—April
Stringfellow, G.B., L1—February
Sturm, J.C., 1051—October
Stutius, W., 59—January
Su, Y.K., 753—July
Sudharsanan, R., 259—March
Sugimoto, Y., 145—February
Sun, J.Y.-C., 721—July
Sune, C.T., 651—July
Swanson, J.G., 13—January
Swanson, L.G., 865—September
Swart, P.L., 809—August
Swart, P.L., 1383—December
Swartz, J.C., 171—February
Swartzlander, A.B., 1061—October

Takahashi, K., 1083—October
Takenaka, T., 801—August
Tandon, S., 89—January
Tasch, A., 375—April
Tasch, A., 1027—October
Tasch, A., 1043—October
Tasch, A., 1089—October
Temkin, H., 1015—October
Temple, D., 995—September
Tessmer, G.J., 509—June
Thakur, R.P.S., 481—May
Thakur, R.P.S., 1061—October
Theil, J.A., 209—March
Theodore, N.D., 821—August
Thompson, C.V., 1155—November
Thompson, C.V., 1207—November
Thompson, J., 323—April
Thompson, J., 349—April
Thompson, M.O., 957—September
Thonke, K., 555—June
Timbrell, P.Y., 657—July
Tompa, G.S., 357—April
Tothill, J.N., 515—June
Townsend, P., 1357—December
Tsu, D.V., 209—March
Tuan, H.C., 19—January
Tuppen C.G., 1101—October
Turner, J.E., 345—April
Turner, J.E., 1425—December
Turton, R.J., 35—January

Ueda, K., 801—August
Ullal, H.S., 481—May
Ulrich, R.K., 419—May
Uneta, M., 219—March

Van Ackere, M., 317—April
Van Daele, P., 317—April
Venkatesan, T., 117—January
Venkatraman, R., 1231—November
Vesely, E.J., 59—January

Wagner, H., 1107—October
Walker, C.J., 617—July

Walker, P.J., 783—August
Walters, M., 711—July
Wang, C.A., 463—May
Wang, K.L., 125—February
Wang, L.K., 721—July
Wang, R.-P., 829—August
Ward, I.D., 265—March
Warren, W.L., 425—May
Watanabe, M., 407—May
Watanabe, Y., 219—March
Watson, G.P., 957—September
Weihs, T.P., 903—September
Weir, B.E., 949—September
Wen X., 539—June
Wendt, J.P., 495—May
Wennekers, P., 555—June
Werner, K., 305—April
Westbrook, L., 515—June
White, M.H., 487—May
Wiedemeier, H., 159—February
Wiedemeier, H., 761—August
Wiedemeier, H., 1303—November
Wiedemeier, H., 1373—December
Wilkens, B., 117—January
Wilkie, J.H., 515—June
Willander, M., 1033—October
Williams, C.K., 651—July
Williams, J.E., 59—January
Williams, P., 1257—November
Winer, K., 241—March
Wolter, K., 471—May
Wong, K.B., 35—January
Woo, J.C.S., 125—February
Woodall, J.M., 283—March
Wordeman, M.R., 721—July
Wortman, J.J., 1129—October
Wowchak, A.M., 561—June
Wrenn, C.S., 1247—November
Wu, C.-C., 197—February
Wu, C.S., 1265—November
Wu, L., 197—February
Wu, M.-M., 197—February
Wu, X., 821—August
Wu, X.D., 117—January

Xie, Y.-H., 949—September
Xu, D.X., 1033—October

Yamada, A., 1083—October
Yamamoto, H., 739—July
Yang, E.S., 821—August
Yeh, J.J., 235—March
Yerke, L., 1247—November
Yoon E., 337—April
Yoon S., 487—May
Young, D.R., 231—March
Yu, K.K., 1265—November
Yu, T.H., 509—June

Zajic, V., 689—July
Zappe, H.P., 747—July
Zawadzki, P.A., 357—April
Zehr, S.W., 1313—November
Zeindl, H.P., 1119—October
Zheng, X.-Y., 581—June
Zheng, Y., 1185—November
Zhong, Y., 1129—October
Zielinski, W., 865—September
Zingg, R.P., 1111—October
Zipperian, T.E., 533—June
Zook J.D., 231—March